

Problem 8: Dielectric constants of wurtzite CdSe

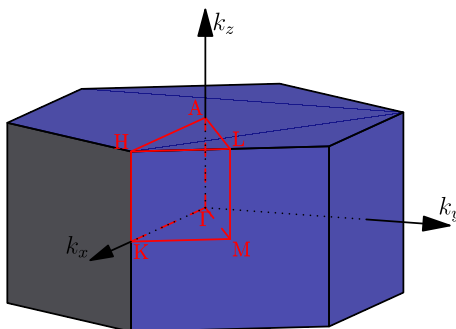
CdSe is a semiconductor with the wurtzite structure. This structure has four atoms in the unit cell. The Cd atoms occupy the hcp sites while the Se atoms are in one half of the tetrahedral sites. Putting the origin in the middle of the bond the Cartesian coordinates of the atoms are:

$$\begin{aligned}
 \mathbf{d}_{Cd_1} &= a(1/2, 1/(2\sqrt{3}), -7c/(16a)), \\
 \mathbf{d}_{Cd_2} &= a(-1/2, -1/(2\sqrt{3}), c/(16a)), \\
 \mathbf{d}_{Se_1} &= a(1/2, 1/(2\sqrt{3}), c(u - 7/16)/a), \\
 \mathbf{d}_{Se_2} &= a(-1/2, -1/(2\sqrt{3}), c(u - 1/16)/a).
 \end{aligned} \tag{1}$$

where for u we take the ideal value $u = 3/8$. The size of the hexagonal Bravais lattice is $a = 8.12$ a.u., $c/a = \sqrt{8/3}$.

The form factors for the wurtzite structure of CdSe are given in Phys. Rev. **164**, 1069 (1967).

1. Modify the CB program in order to deal with the wurtzite structure and to use the form factors given in the above reference.
2. Modify the CB program in order to calculate the reciprocal lattice vectors of the hexagonal lattice of ZnS. The Brillouin zone and a few high symmetry points are shown in the figure:



3. Compare your results with Fig. 2 of the above reference.
4. Compute the imaginary part of dielectric constant of CdS as a function of frequency and plot it. The expression of the imaginary part of the dielectric constant, in c.g.s. units is:

$$\epsilon_2(\omega) = \frac{e^2}{\pi m^2 \omega^2} \sum_{v,c} \int_{BZ} \delta(\epsilon_c(\mathbf{k}) - \epsilon_v(\mathbf{k}) - \hbar\omega) |p_{vc}|^2 d^3k \tag{2}$$

where $p_{vc} = -i\hbar \langle \psi_v(\mathbf{k}) | \frac{d}{dz} | \psi_c(\mathbf{k}) \rangle$ is the matrix element of the p_z operator between the the valence and conduction Bloch functions. Compare with Fig.9 of the above reference.